

SAMYANG ELECTRONICS

(SINGLE CHIP) MBR820 --- MBR8200

SCHOTTKY BARRIER RECTIFIER

FEATURES

- \bigotimes Metal-semiconductor junction with guard ring
- \bigcirc Epitaxial construction
- \bigotimes Low forward voltage drop,low switching losses
- \bigcirc High surge capability
- ◇ For use in low voltage, high frequency inverters free wheeling, and polarity protection applications
- \bigcirc The plastic material carries U/L recognition 94V-0

MECHANICAL DATA

- - MIL-STD-750,Method 2026
- ♦ Weight: 0.08ounces, 2.24 grams
- ♦ Mounting position: Any

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 $^\circ\!\!\! C$ ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

	Symbols	MBR 820	MBR 830	MBR 840	MBR 850	MBR 860	MBR 880	MBR 8100	MBR 8150	MBR 8200	Units
Maximum repetitive peak reverse voltage	Vrrm	20	30	40	50	60	80	100	150	200	Volts
Maximum RMS voltage	Vrms	14	21	28	35	42	56	70	105	140	Volts
Maximum DC blocking voltage	Vdc	20	30	40	50	60	80	100	150	200	Volts
Maximum average forwardPer legrectified current(see Fig.1)Total device	I(AV)	4.0 8.0									Amps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	IFSM	150.0								Amps	
Maximum instantaneous forward voltage at 8.0 A(Notes 1)	VF	0. 60			C	0.75	0.85		0.90	0.95	Volts
$ \begin{array}{c} \mbox{Maximum instantaneous reverse} \\ \mbox{current at rated DC blocking} \\ \mbox{voltage(Notes 1)} \end{array} \qquad \begin{array}{c} T_{\text{A}} = 25^{\circ}\mbox{C} \\ \hline T_{\text{A}} = 125^{\circ}\mbox{C} \end{array} $	I-	0.2									mA
	R	15 50									
Typical thermal resistance (Notes 2)	R_{θ} JC	2.5								° C/W	
Operating junction temperature range	TJ	-65 to+150									°C
Storage temperature range	Tstg	-65 to+150									°С

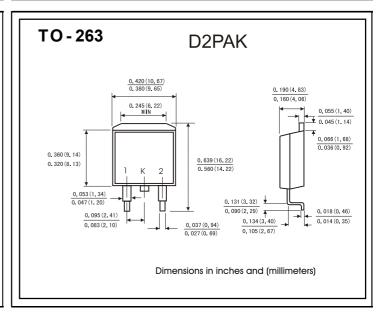
NOTE: 1. Pulse test:300us pulse width,1% duty cycle.

2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

3. Thermal resistance junction to ambient

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VOLTAGE RANGE: 20 --- 200 V CURRENT: 8.0A



RATINGS AND CHARACTERISTIC CURVES

FIG.1-FORWARD CURRENT DERATING CURVE AVERAGE FORWARD CURRENT AMPERES 5.0 4.0 3. 0

INDUCTIVE OR RESISTIVE LOAD 100 LEAD TEMPERATURE (*C)

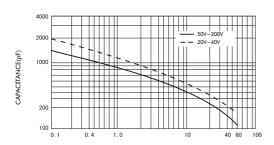
150

2.0

1.0

0 l 0 SINGLE PHASE HALF WAVE 50

FIG.4-TYPICAL JUNCTION CAPACITANCE



REVERSE VOLTAGE (VOLTS)

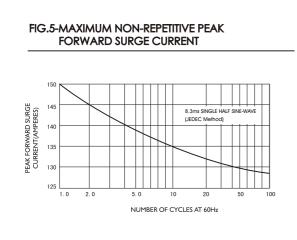
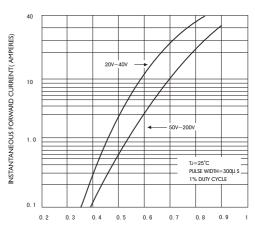
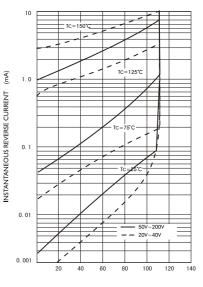


FIG.2-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS



INSTANTANEOUS FORWARD VOLTAGE (VOLTS)

FIG.3-TYPICAL REVERSE CHARACTERISTICS



PERCENT OF RATED PEAK REVERSE VOLTAGE (VOLTS)

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